

ABSTRACT

The present invention provide an LDD type TFT having excellent properties, particularly for a liquid crystal display unit. For this purpose, a top gate type LDDTFT gate electrode is converted into a two-stage structure by use of a chemical reaction or plating, and furthermore, into a shape in which an upper portion or a lower portion slightly protrudes on the source electrode side, or the drain electrode side relative to the other portions. Impurities are injected by using this electrode having this structure and shape as a mask. Prior to injection of impurities, the gate insulating film is removed, and a Ti film is formed for preventing hydrogen for dilution from coming in. This is also the case with the LDD-TFT on the bottom gate side.

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